

PHOTOMASK AND METHOD FOR REDUCING EXPOSURE TIMES
OF HIGH DENSITY PATTERNS ON THE SAME

ABSTRACT OF THE DISCLOSURE

A method for reducing exposure times for high density patterns on a photomask is disclosed. The method includes moving a selected feature located in a cell
5 between a first boundary and a second boundary from a first pattern file to a second pattern file and exposing a resist layer of a photomask blank with the first pattern file by using a step and repeat technique.